



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Description

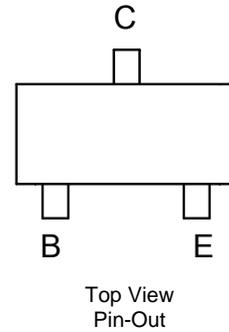
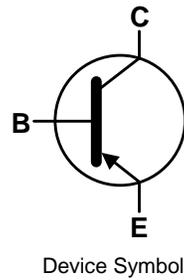
The NK-AC857BQ-NK-AC857CQ Bipolar Junction Transistors (BJT) are designed to meet the stringent requirements of Automotive Applications.

Features

- Ideally Suited for Automatic Insertion
- Complementary NPN Types: AC847BQ-AC847CQ
- For Switching and AF Amplifier Applications

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per
MIL-STD-202, Method 208 (e3)
- Weight: 0.008 grams (Approximate)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-45	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Continuous Collector Current	I _C	-100	mA
Peak Collector Current	I _{CM}	-200	mA
Peak Emitter Current	I _{EM}	-200	mA
Peak Base Current	I _{BM}	-200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

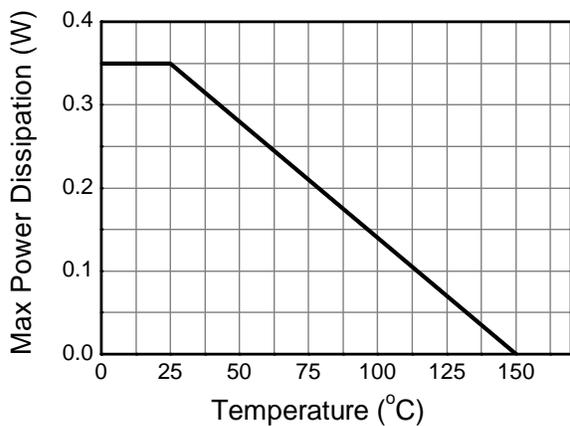
Characteristic	Symbol	Value	Unit
Power Dissipation	P _D	(Note 6)	310
		(Note 7)	350
Thermal Resistance, Junction to Ambient	R _{θJA}	(Note 6)	403
		(Note 7)	357
Thermal Resistance, Junction to Leads	R _{θJL}	350	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

ESD Ratings (Note 9)

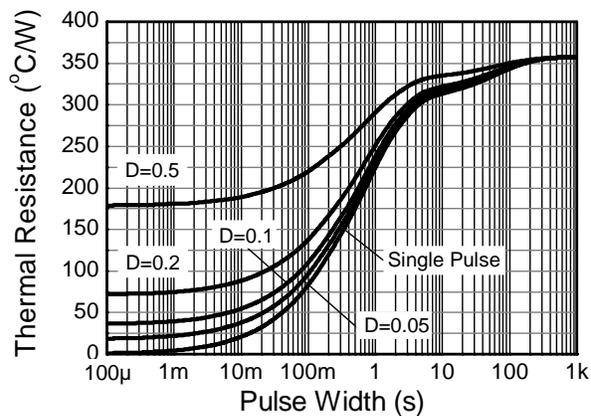
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 7. Same as Note 6, except the device is mounted on 15mm x 15mm 1oz copper.
 8. Thermal resistance from junction to solder-point (at the end of the leads).
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

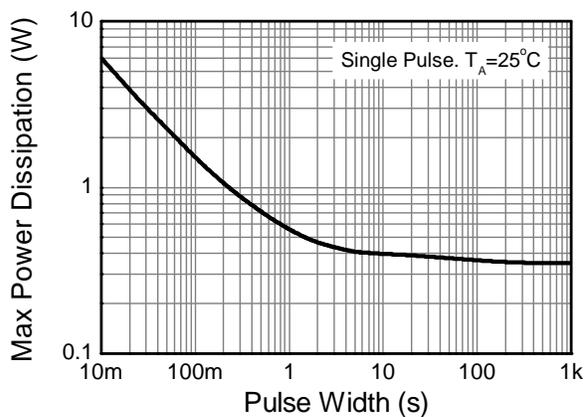
Thermal Characteristics and Derating Information



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-50	—	—	V	I _C = -10μA
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-45	—	—	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	—	—	V	I _E = -1μA
Collector Cutoff Current	I _{CBO}	—	—	-15	nA	V _{CB} = -30V
				-4	μA	V _{CB} = -30V, T _J = +150°C
Collector Emitter Cutoff Current	I _{CES}	—	—	-15	nA	V _{CE} = -50V
Emitter-Base Cutoff Current	I _{EBO}	—	—	-100	nA	V _{EB} = -5V
Small Signal Current Gain (Note 10)	NK-AC857BQ	—	330	—	—	I _C = -2.0mA, V _{CE} = -5V f = 1.0kHz
	NK-AC857CQ	—	600	—	—	
Input Impedance (Note 10)	NK-AC857BQ	—	4.5	—	kΩ	
	NK-AC857CQ	—	8.7	—	—	
Output Admittance (Note 10)	NK-AC857BQ	—	30	—	μS	
	NK-AC857CQ	—	60	—	—	
Reverse Voltage Transfer Ratio (Note 10)	NK-AC857BQ	—	2×10 ⁻⁴	—	—	
	NK-AC857CQ	—	3×10 ⁻⁴	—	—	
DC Current Gain (Note 10)	NK-AC857BQ	220	290	475	—	
	NK-AC857CQ	420	520	800	—	
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(SAT)}	—	-75	-300	mV	I _C = -10mA, I _B = -0.5mA
			-250	-650	mV	I _C = -100mA, I _B = -5.0mA
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(ON)}	-600	-650	-750	mV	I _C = -2mA, V _{CE} = -5V
			—	-820	mV	I _C = -10mA, V _{CE} = -5V
Base-Emitter Saturation Voltage (Note 10)	V _{BE(SAT)}	—	-700	—	mV	I _C = -10mA, I _B = -0.5mA
			-850	-1100	mV	I _C = -100mA, I _B = -5mA
Output Capacitance	C _{obo}	—	3	—	pF	V _{CB} = -10V, f = 1.0MHz
Transition Frequency	f _T	100	200	—	MHz	V _{CE} = -5V, I _C = -10mA, f = 100MHz
Noise Figure	NF	—	2	10	dB	V _{CE} = -5V, I _C = -200μA R _S = 2kΩ, f = 1kHz Δf = 200Hz

Note: 10. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

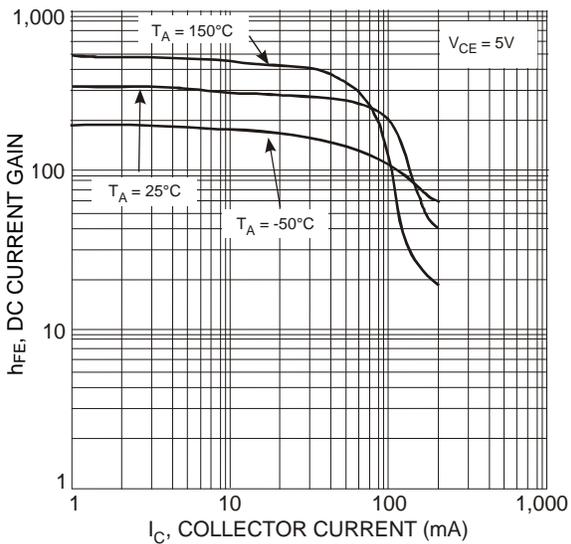


Figure 1 Typical DC Current Gain vs. Collector Current

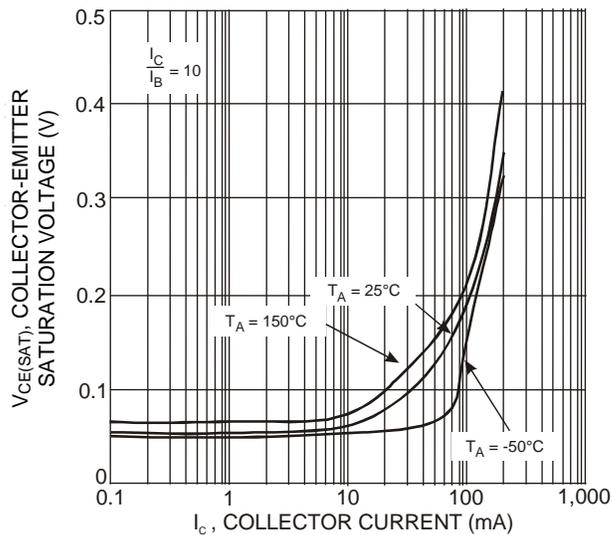


Figure 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current

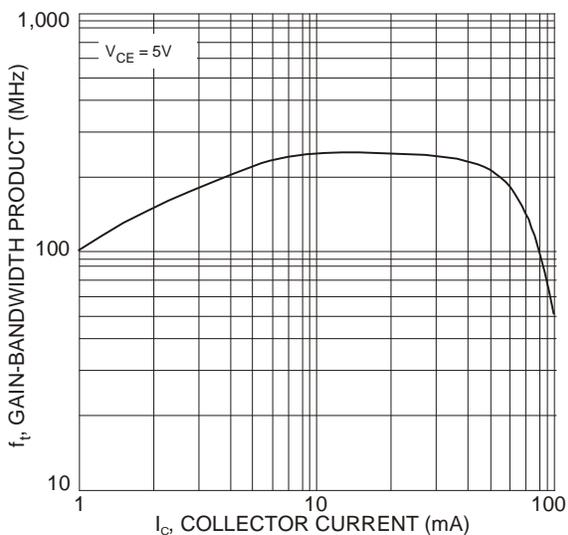
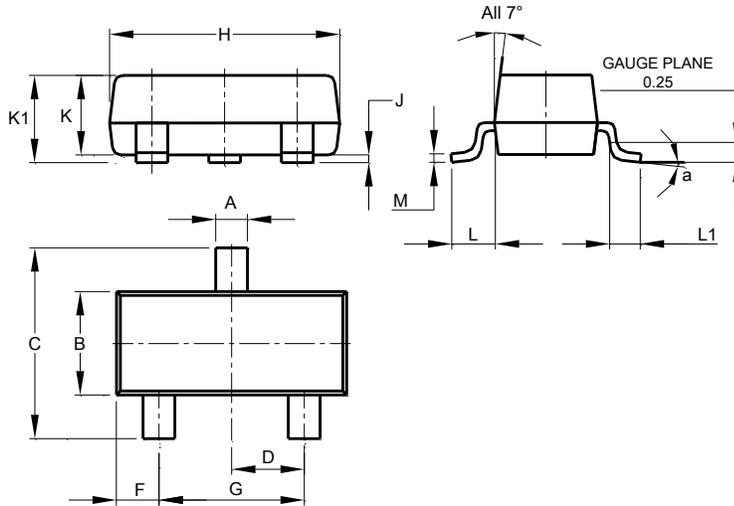


Figure 3 Gain-Bandwidth Product vs Collector Current

Package Outline Dimensions

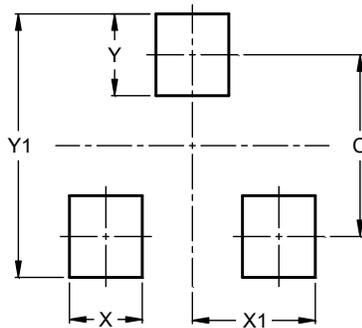
SOT23



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9